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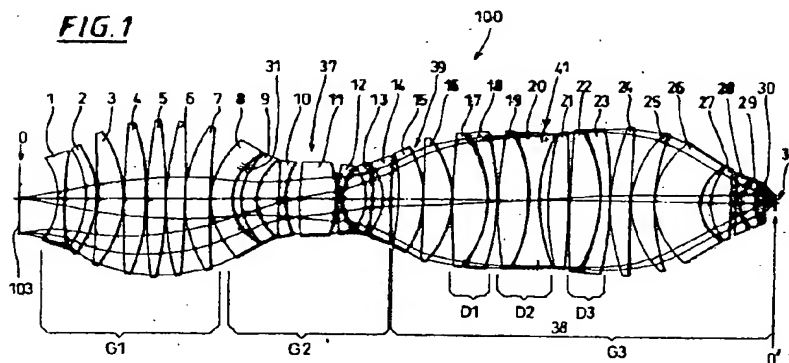
(54) **Optical projection lens system**

(57) An optical projection lens system comprising in direction of propagating radiation

- a first lens group having positive refractive power
- a second lens group having negative refractive power and comprises a waist with a minimum diameter of the propagating radiation

- a further lens arrangement with positive refracting power, which follows the second lens group, wherein at least one lens of the projection lens system, which is arranged in front of the waist comprises an aspherical surface.

FIG.1



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Description

Field of the invention

[0001] This invention generally relates to an optical projection system comprising a light source, a mask holder, a projection lens system, and specifically relates to an optical projection system for photolithography used in producing micro structured devices such as integrated circuits or other semiconductor devices. During the fabrication of such devices photolithography transfers an image from an photographic mask to a resultant pattern on a semiconductor wafer. Such photolithography generally includes a light exposure process, in which a semiconductor wafer is exposed to light having information of a mask pattern. Optical projection systems are used to perform the light exposure process.

[0002] In general, the transferred mask patterns are very fine, so that optical projection lens systems are required to have a high resolution. The high resolution necessitates a large numerical aperture of the optical projection lens system and also a nearly no aberration of the optical projection lens system in the light exposure field.

Related background art

[0003] For example some projection lens system are proposed in the German Patent-Application DE 198 18 444 A1. The shown projection lens system comprises 6 lens groups. The first, third, fifth and the sixth lens groups have positive refractive power and the second and fourth lens groups have negative refractive power. To get a high resolution in all shown examples, aspherical surfaces are in the fourth and fifth lens groups.

[0004] Some purely refractive projection exposure objectives of microlithography are discussed in SPIE Vol.237(1980) page 310 ff.. There are shown objectives of the planar style and the distagon style, wherein the new style of objectives comprises two waists for petzval correction.

Summary of the invention:

[0005] It is an object of this invention to provide a further excellent optical projection lens system for photolithography.

[0006] The optical projection lens system of the invention comprises in a direction of the light a first lens group having positive refractive power and a second lens group having negative refractive power and establishing a beam waist of minimal beam height. A further lens arrangement follows the second lens group. At least one lens, which is arranged before first beam waist, has an aspherical surface. Further lenses comprising aspherical surfaces in all other groups will be helpful to reduce the needed amount of material and to reduce the length of the optical projection lens system.

Brief descriptions of the drawing

[0007]

Figure 1 is a cross section of an optical projection lens system according to an embodiment of the invention with only one clearly defined waist;

[0008] The optical projection lens system, shown in figure 1 comprises 30 lenses 1 - 30. This shown projection lens system is for wafer manufacture. For illuminating a mask 103, which is positioned at 0, a light source with a narrow bandwidth is used. In this example an excimer laser, which is not shown in the drawing, is used. The shown projection lens system is capable to be operated at 193,3 nm with a high numerical aperture of 0.7. This projection lens system is also adaptable to be operated at $\lambda = 248$ nm or $\lambda = 157$ nm.

[0009] A projection system comprising with this projection lens system the scale of the mask 103 projected on a wafer is reduced, wherein the wafer is positioned on 0'. The factor of scale reduction is 4 and the distance of 0 to 0' is 1000 mm. The illuminated image field is rectangular, e.g. 7 x 20 to 15 x 30 mm².

[0010] The present invention will be more fully understood from the detailed description given below and the accompanying drawing.

[0011] In direction of propagating radiation this projection lens system comprises a first lens group G1 comprising lenses 1 to 7 and a second lens group G2 comprising lenses 8 to 14, and a further lens arrangement G3 comprising lenses 15 to 30. The first lens group G1 has positive refractive power and ends with a lens 7 of positive refractive power.

[0012] The first lens 8 of the second lens group G2 is the first lens 8 behind the first belly of the projection lens system 100, which has a concave shaped lens surface 31 on the image side. In the shown example, this concave surface 31 has an aspherical shape. This aspherical surface 31 helps to reduce the track length, the number of needed lenses and to get a high image quality over the whole illuminated image field.

[0013] This second lens group G2 has negative refractive power and comprises a clearly defined waist 37, which comprises seven lenses. The high number of lenses are needed for petzval correction, because there is only one clearly defined waist. There are three negative lenses 8-10 arranged in front of a lens 11 of positive refractive power in the middle of the lens group G2. Behind this positive lens 11 there are further three negative lenses 12-15.

[0014] The first lens 15 of the following lens arrangement G3 has positive refractive power. This is the first lens 15 of positive refractive power behind the lens 11 in the middle of the lens group G2. This lens arrangement G3 has positive refractive power and comprises lenses 15-30 of different materials and an aperture stop 41.

[0015] Especially CaF_2 lenses 16, 17, 19, 21, 22, 29 and 30 are used. The other lenses are of quartz glass. These CaF_2 lenses are especially used for correction of chromatic aberration. This system comprises doublets D1, D2 and D3, which comprise a CaF_2 lens with positive refractive power followed by a quartz glass lens of negative refractive power. If no correction of chromatic aberration is required, as usual in 248 nm systems, or possible with very narrow laser bandwidth, there can be taken single lenses instead of the doublets D1 - D3 with the advantage of reducing the needed material and lenses.

[0016] A very shallow waist 37 is recognizable between lens 20 and lens 21.

[0017] The lens arrangement G3 has an maximal diameter of 238 mm.

[0018] The lens data of this embodiment are listed in table 1. The aspheric surface is described mathematically by:

$$P(h) = \frac{\delta \cdot h^2}{1 + \sqrt{1 - (1 - EX) \cdot \delta^2 \cdot h^2}} + C_1 h^4 + \dots + C_n h^{2n+2}$$

with $\delta = 1/R$, wherein R is the paraxial curvature and P is the sag as a function of the radius h.

[0019] The maximal beam diameter is 238 mm and the track length is 1000 mm, wherein the numerical aperture is $NA = 0,7$. This effects a very compact construction with reduced cost for lens material.

[0020] The implementation of CaF_2 lenses 16, 17, 19, 21, 22 effects a good correction of chromatic aberration of this compact embodiment. The last two CaF_2 lenses 29, 30 at the end of the lens arrangement G3 are inserted for their resistance versus compaction.

[0021] As those skilled in the art of optical projection lens systems will readily appreciate numerous substitutions, modifications and additions may be made to the above design without departing from the spirit and scope of the present invention. It is intended that all such substitutions, modifications, and additions fall within the scope of the invention, which is defined by the claims.

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	Linsen	RADIEN	DICKEN	GLAESER
5		UNENDL	17,52	
	L1	-116,39	10,00	SiO ₂
		617,53	31,49	
	L2	-143,96	15,00	SiO ₂
		-158,71	0,50	
10	L3	-1180,69	37,72	SiO ₂
		-191,12	0,50	
	L4	2484,02	31,18	SiO ₂
		-409,87	0,50	
15	L5	864,05	28,13	SiO ₂
		-720,08	0,50	
	L6	566,89	25,00	SiO ₂
		-5256,53	0,50	
	L7	230,42	36,66	SiO ₂
20		1542,90	0,50	
	L8	132,99	31,60	SiO ₂
		84,39	12,54	
	L9	101,03	22,70	SiO ₂
		80,07	30,80	
25	L10	-7281,27	10,00	SiO ₂
		139,12	20,25	
	L11	962,49	53,36	SiO ₂
		-190,49	0,50	
30	L12	348,09	9,00	SiO ₂
		96,42	32,28	
	L13	-94,72	11,00	SiO ₂
		-203,97	14,37	
	L14	-91,49	13,00	SiO ₂
35		4787,89	10,28	
	L15	-329,06	36,69	SiO ₂
		-173,40	0,50	
	L16	-2176,02	40,00	CaF ₂
40		-161,94	1,00	
	L17	1885,09	50,00	CaF ₂
		-195,36	0,48	
	L18	-198,97	15,00	SiO ₂
		-389,14	0,50	
45	L19	687,29	45,10	CaF ₂
		-254,11	0,10	
	L20	-261,96	15,00	SiO ₂
		261,17	13,27	
50	L21	530,40	32,00	CaF ₂
		-1166,11	0,50	
	L22	1879,17	45,00	CaF ₂
		-237,88	0,10	
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	L23	-271,21	15,00	SiO ₂
		-609,73	0,50	
5	L24	351,48	30,00	SiO ₂
		100200,00	0,50	
	L25	157,95	34,26	SiO ₂
		329,33	0,50	
10	L26	125,26	67,46	SiO ₂
		69,91	16,27	
	L27	102,35	30,27	SiO ₂
		-1072,95	7,25	
15	L28	-914,82	5,00	SiO ₂
		63,74	0,50	
	L29	53,45	23,33	CaF ₂
		82,67	0,50	
20	L30	60,16	10,70	CaF ₂
		1256,42	15,34	

asph. Konstanten

$$EX = 0,139140 \cdot 10^{-8}$$

$$C_1 = 0,178710 \cdot 10^{-12}$$

$$C_2 = 0,601290 \cdot 10^{-17}$$

$$C_3 = 0,253200 \cdot 10^{-20}$$

Claims

1. An optical projection lens system for microlithography comprising in direction of propagating radiation

- a first lens group having positive refractive power,
- a second lens group having negative refractive power and comprising a waist with a minimum diameter of the propagating radiation,
- a further lens arrangement with positive refracting power, which follows the second lens group, wherein lenses, which comprises an aspherical surface, are arranged in front of the waist.

2. An optical projection lens system for microlithography comprising in direction of propagating radiation

- a first lens group having positive refractive power,
- a second lens group having negative refractive power and comprising a waist with a minimum diameter of propagating radiation,
- a further lens arrangement with positive refracting power, which follows the second lens group, wherein the projection lens system comprises only one clearly defined waist and

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wherein at least one lens comprises an aspherical surface.

3. An optical projection lens system for microlithography comprising in direction of propagating radiation

- a first lens group having positive refractive power,
- a second lens group having negative refractive power and comprising a waist with a minimum diameter of the propagating radiation,
- a further lens arrangement with positive refracting power, which follows the second lens group, wherein the projection lens system comprises only one clearly defined waist, wherein the numerical aperture is greater than 0.65.

4. An optical projection lens system of claim 1 or 2 or 3, wherein only the second lens group comprises an aspherical surface.

5. An optical projection lens system of claim 1 or 2 or 3, wherein the lens arrangement comprises a second shallow waist.

6. An optical projection lens system of claim 1 or 2 or 3, wherein the lens comprising the aspherical surface is an meniscus shaped lens.

7. An optical projection lens system of at least one of the claims 1 to 6, wherein at least a second material is used for chromatic correction.

8. An optical projection lens system of at least one of the claims 1 to 7, wherein the first material is quartz glass and wherein the second material is a fluoride.

9. An optical projection lens system of claims 1 to 8, wherein the second material is used in the positive lens elements nearby the aperture stop.

10. An optical projection lens system of claims 1 to 9, wherein CaF_2 is the second material used for 193 nm.

11. An optical projection lens system of claim 1 or 2 or 3, wherein at least two of the lenses of the lens arrangement in front of the aperture stop are of CaF_2 .

12. An optical projection lens system of at least one of claims 1 to 11, wherein the numerical aperture on the image side of the projection lens system is greater than 0.65, preferable 0,7 and more.

13. An optical projection lens system of at least one of the claims 1 to 12, wherein at least three CaF_2 lenses are bi-convex lenses.

14. An optical projection lens system of at least one of the claims 1 to 13, wherein the last lens element is a CaF_2 lens.

15. An optical projection lens system of at least one of the claims 1 to 14, wherein an excimer laser is used as a light source emitting radiation of 250 nm and shorter wavelength.

16. An optical projection lens system of at least one of the claims 1 to 15, wherein the optical projection lens system comprises only two bellies.

17. Process for producing microstructured devices, wherein a wafer with a light sensitive layer is exposed by UV- light using an optical projection lens system of one of the claims 1 to 14 and using a mask for defining the structure of the device, wherein the light sensitive layer is developed to get the microstructured device.

FIG. 1

